



PATENT  
Attorney Docket No.: 018865-015200US  
Client Reference No.: 17732-67340.00

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

Daniel Calafut et al.

Application No.: 10/801,499

Filed: March 15, 2004

For: MONOLITHICALLY INTEGRATED  
TRENCH POWER MOSFET AND  
SCHOTTKY DIODE (as amended)

Group Director: 2814

Confirmation No.: 1835

Examiner: Anh D. Mai

Art Unit: 2814

SUPPLEMENTAL INFORMATION  
DISCLOSURE STATEMENT UNDER 37  
CFR §1.97 and §1.98

**Mail Stop RCE**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

August 29, 2006

Sir:

The references cited on attached form PTO/SB/08A&B are being called to the attention of the Examiner. Copies of the references in compliance with the requirements of 37 CFR §1.98(a)(2) are enclosed. Also enclosed is a copy of the **International Search Report** corresponding to the PCT application.

It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

As provided for by 37 CFR §1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information.

This IDS is being filed on or before payment of the issue fee.

**CERTIFICATION**

I hereby certify that each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

Respectfully submitted,

Barmak Sani  
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/801,499
				Filing Date	March 15, 2004
				First Named Inventor	Calafut, Daniel
				Art Unit	2814
Sheet	1	of	1	Examiner Name	Anh D. Mai
				Attorney Docket Number	018865-015200US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-2002-0125528 A1	09-12-2002	Kawaguchi et al.	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
								<input type="checkbox"/>

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	2	Cheng, "Fast Reverse Recovery Body Diode in High-Voltage VDMOSFET using Cell-Distributed Schottky Contacts", IEEE Transactions on Electron Devices, Volume: 40, Issue: 7, pp. 1422-1425, May 5, 2003	<input type="checkbox"/>
	3	Tu et al., "Controlling the characteristics of the MPS rectifier by variation of area of Schottky region", IEEE Transactions on Electron Devices, Volume: 40, Issue: 7, pp. 1307-1315, July 7, 1993	<input type="checkbox"/>

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.